

PrimePACK™3+ B-series module with Trench/Fieldstop IGBT5, emitter controlled 5 diode and NTC

Features

- Electrical features
 - $V_{CES} = 1700\text{ V}$
 - $I_{C\text{ nom}} = 2000\text{ A} / I_{CRM} = 4000\text{ A}$
 - Low switching losses
 - High current density
 - High surge current capability
 - $T_{vj,op} = 175^{\circ}\text{C}$
- Mechanical features
 - High power and thermal cycling capability
 - High power density
 - High creepage and clearance distances
 - Package with CTI > 400



Potential applications

- Wind turbines
- High-power converters
- Motor drives

Product validation

- Qualified for industrial applications according to the relevant tests of IEC 60747, 60749 and 60068

Description

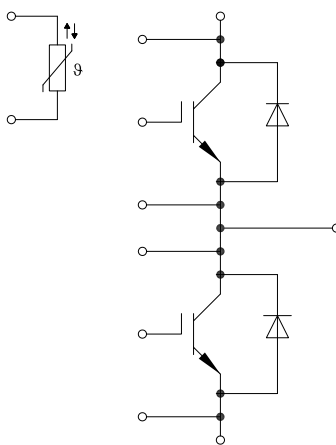


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1 Package

Table 1 Insulation coordination

Parameter	Symbol	Note or test condition	Values	Unit
Isolation test voltage	V_{ISOL}	RMS, $f = 50 \text{ Hz}$, $t = 60 \text{ s}$	4.0	kV
Material of module baseplate			Cu	
Creepage distance	d_{Creep}	terminal to heatsink	36.0	mm
Creepage distance	d_{Creep}	terminal to terminal	28.0	mm
Clearance	d_{Clear}	terminal to heatsink	21.0	mm
Clearance	d_{Clear}	terminal to terminal	19.0	mm
Comparative tracking index	CTI		> 400	

Table 2 Characteristic values

Parameter	Symbol	Note or test condition	Values			Unit
			Min.	Typ.	Max.	
Stray inductance module	L_{sCE}			10		nH
Module lead resistance, terminals - chip	$R_{AA'+CC'}$	$T_C = 25 \text{ °C}$, per switch		0.12		mΩ
Module lead resistance, terminals - chip	$R_{CC'+EE'}$	$T_C = 25 \text{ °C}$, per switch		0.13		mΩ
Storage temperature	T_{stg}		-40		150	°C
Maximum baseplate operation temperature	T_{BPmax}				150	°C
Mounting torque for module mounting	M	- Mounting according to valid application note	M5, Screw	3	6	Nm
Terminal connection torque	M	- Mounting according to valid application note	M4, Screw	1.8	2.1	Nm
			M8, Screw	8	10	
Weight	G			1400		g

2 IGBT, Inverter

Table 3 Maximum rated values

Parameter	Symbol	Note or test condition		Values	Unit
Collector-emitter voltage	V_{CES}		$T_{vj} = 25 \text{ °C}$	1700	V
Implemented collector current	I_{CN}			2000	A
Continuous DC collector current	I_{CDC}	$T_{vj \text{ max}} = 175 \text{ °C}$	$T_C = 90 \text{ °C}$	2000	A

(table continues...)

Table 3 (continued) Maximum rated values

Parameter	Symbol	Note or test condition	Values	Unit
Repetitive peak collector current	I_{CRM}	t_p limited by $T_{vj\ op}$	4000	A
Gate-emitter peak voltage	V_{GES}		± 20	V

Table 4 Characteristic values

Parameter	Symbol	Note or test condition	Values			Unit
			Min.	Typ.	Max.	
Collector-emitter saturation voltage	$V_{CE\ sat}$	$I_C = 2000\ A, V_{GE} = 15\ V$	$T_{vj} = 25\ ^\circ C$	1.90	2.27	V
			$T_{vj} = 125\ ^\circ C$	2.30	2.64	
			$T_{vj} = 175\ ^\circ C$	2.45	2.82	
Gate threshold voltage	V_{GEth}	$I_C = 72\ mA, V_{CE} = V_{GE}, T_{vj} = 25\ ^\circ C$	5.35	5.80	6.25	V
Gate charge	Q_G	$V_{GE} = \pm 15\ V, V_{CC} = 900\ V$		8.5		μC
Internal gate resistor	R_{Gint}	$T_{vj} = 25\ ^\circ C$		0.75		Ω
Input capacitance	C_{ies}	$f = 100\ kHz, T_{vj} = 25\ ^\circ C, V_{CE} = 25\ V, V_{GE} = 0\ V$		101		nF
Reverse transfer capacitance	C_{res}	$f = 100\ kHz, T_{vj} = 25\ ^\circ C, V_{CE} = 25\ V, V_{GE} = 0\ V$		3.5		nF
Collector-emitter cut-off current	I_{CES}	$V_{CE} = 1700\ V, V_{GE} = 0\ V, T_{vj} = 125\ ^\circ C$			10	mA
Gate-emitter leakage current	I_{GES}	$V_{CE} = 0\ V, V_{GE} = 20\ V, T_{vj} = 25\ ^\circ C$			400	nA
Turn-on delay time (inductive load)	t_{don}	$I_C = 2000\ A, V_{CC} = 900\ V, V_{GE} = \pm 15\ V, R_{Gon} = 0.3\ \Omega$	$T_{vj} = 25\ ^\circ C$	0.285		μs
			$T_{vj} = 125\ ^\circ C$	0.300		
			$T_{vj} = 175\ ^\circ C$	0.310		
Rise time (inductive load)	t_r	$I_C = 2000\ A, V_{CC} = 900\ V, V_{GE} = \pm 15\ V, R_{Gon} = 0.3\ \Omega$	$T_{vj} = 25\ ^\circ C$	0.160		μs
			$T_{vj} = 125\ ^\circ C$	0.175		
			$T_{vj} = 175\ ^\circ C$	0.185		
Turn-off delay time (inductive load)	t_{doff}	$I_C = 2000\ A, V_{CC} = 900\ V, V_{GE} = \pm 15\ V, R_{Goff} = 1.1\ \Omega$	$T_{vj} = 25\ ^\circ C$	0.765		μs
			$T_{vj} = 125\ ^\circ C$	0.875		
			$T_{vj} = 175\ ^\circ C$	0.925		
Fall time (inductive load)	t_f	$I_C = 2000\ A, V_{CC} = 900\ V, V_{GE} = \pm 15\ V, R_{Goff} = 1.1\ \Omega$	$T_{vj} = 25\ ^\circ C$	0.115		μs
			$T_{vj} = 125\ ^\circ C$	0.270		
			$T_{vj} = 175\ ^\circ C$	0.385		
Turn-on energy loss per pulse	E_{on}	$I_C = 2000\ A, V_{CC} = 900\ V, L_\sigma = 30\ nH, V_{GE} = \pm 15\ V, R_{Gon} = 0.3\ \Omega, di/dt = 10700\ A/\mu s (T_{vj} = 175\ ^\circ C)$	$T_{vj} = 25\ ^\circ C$	335		mJ
			$T_{vj} = 125\ ^\circ C$	485		
			$T_{vj} = 175\ ^\circ C$	575		

(table continues...)

Table 4 (continued) Characteristic values

Parameter	Symbol	Note or test condition	Values			Unit
			Min.	Typ.	Max.	
Turn-off energy loss per pulse	E_{off}	$I_C = 2000\text{ A}$, $V_{CC} = 900\text{ V}$, $L_\sigma = 30\text{ nH}$, $V_{GE} = \pm 15\text{ V}$, $R_{Goff} = 1.1\text{ }\Omega$, $dv/dt = 2400\text{ V}/\mu\text{s}$ ($T_{vj} = 175\text{ }^\circ\text{C}$)	$T_{vj} = 25\text{ }^\circ\text{C}$	425		mJ
			$T_{vj} = 125\text{ }^\circ\text{C}$	590		
			$T_{vj} = 175\text{ }^\circ\text{C}$	690		
SC data	I_{SC}	$V_{GE} \leq 15\text{ V}$, $V_{CC} = 1000\text{ V}$, $V_{CEmax} = V_{CES} - L_{sCE} \cdot di/dt$	$t_P \leq 10\text{ }\mu\text{s}$, $T_{vj} \leq 175\text{ }^\circ\text{C}$	9200		A
Thermal resistance, junction to case	R_{thJC}	per IGBT			15.0	K/kW
Thermal resistance, case to heat sink	R_{thCH}	per IGBT, $\lambda_{grease} = 1\text{ W}/(\text{m}\cdot\text{K})$		9.70		K/kW
Temperature under switching conditions	$T_{vj\text{ op}}$		-40		175	$^\circ\text{C}$

3 Diode, Inverter

Table 5 Maximum rated values

Parameter	Symbol	Note or test condition	Values	Unit
Repetitive peak reverse voltage	V_{RRM}	$T_{vj} = 25\text{ }^\circ\text{C}$	1700	V
Continuous DC forward current	I_F		2000	A
Repetitive peak forward current	I_{FRM}	$t_P = 1\text{ ms}$	4000	A
I^2t - value	I^2t	$t_P = 10\text{ ms}$, $V_R = 0\text{ V}$	$T_{vj} = 125\text{ }^\circ\text{C}$	kA ² s
			$T_{vj} = 175\text{ }^\circ\text{C}$	
Maximum power dissipation	P_{RQM}	$T_{vj} = 175\text{ }^\circ\text{C}$	1300	kW

Table 6 Characteristic values

Parameter	Symbol	Note or test condition	Values			Unit
			Min.	Typ.	Max.	
Forward voltage	V_F	$I_F = 2000\text{ A}$, $V_{GE} = 0\text{ V}$	$T_{vj} = 25\text{ }^\circ\text{C}$	2.00	2.23	V
			$T_{vj} = 125\text{ }^\circ\text{C}$	2.05	2.33	
			$T_{vj} = 175\text{ }^\circ\text{C}$	2.00	2.32	
Peak reverse recovery current	I_{RM}	$V_{CC} = 900\text{ V}$, $I_F = 2000\text{ A}$, $V_{GE} = -15\text{ V}$, $-di_F/dt = 11500\text{ A}/\mu\text{s}$ ($T_{vj} = 175\text{ }^\circ\text{C}$)	$T_{vj} = 25\text{ }^\circ\text{C}$	1500		A
			$T_{vj} = 125\text{ }^\circ\text{C}$	1760		
			$T_{vj} = 175\text{ }^\circ\text{C}$	1920		

(table continues...)

Table 6 (continued) Characteristic values

Parameter	Symbol	Note or test condition	Values			Unit
			Min.	Typ.	Max.	
Recovered charge	Q_r	$V_{CC} = 900 \text{ V}$, $I_F = 2000 \text{ A}$, $V_{GE} = -15 \text{ V}$, $-di_F/dt = 11500 \text{ A}/\mu\text{s}$ ($T_{vj} = 175 \text{ }^\circ\text{C}$)	$T_{vj} = 25 \text{ }^\circ\text{C}$	315		μC
			$T_{vj} = 125 \text{ }^\circ\text{C}$	595		
			$T_{vj} = 175 \text{ }^\circ\text{C}$	510		
Reverse recovery energy	E_{rec}	$V_{CC} = 900 \text{ V}$, $I_F = 2000 \text{ A}$, $V_{GE} = -15 \text{ V}$, $-di_F/dt = 11500 \text{ A}/\mu\text{s}$ ($T_{vj} = 175 \text{ }^\circ\text{C}$)	$T_{vj} = 25 \text{ }^\circ\text{C}$	190		mJ
			$T_{vj} = 125 \text{ }^\circ\text{C}$	390		
			$T_{vj} = 175 \text{ }^\circ\text{C}$	525		
Thermal resistance, junction to case	R_{thJC}	per diode			38.6	K/kW
Thermal resistance, case to heat sink	R_{thCH}	per diode, $\lambda_{grease} = 1 \text{ W}/(\text{m}\cdot\text{K})$		14.2		K/kW
Temperature under switching conditions	$T_{vj op}$		-40		175	$^\circ\text{C}$

4 NTC-Thermistor

Table 7 Characteristic values

Parameter	Symbol	Note or test condition	Values			Unit
			Min.	Typ.	Max.	
Rated resistance	R_{25}	$T_{NTC} = 25 \text{ }^\circ\text{C}$		5		k Ω
Deviation of R_{100}	$\Delta R/R$	$T_{NTC} = 100 \text{ }^\circ\text{C}$, $R_{100} = 493 \text{ } \Omega$	-5		5	%
Power dissipation	P_{25}	$T_{NTC} = 25 \text{ }^\circ\text{C}$			20	mW
B-value	$B_{25/50}$	$R_2 = R_{25} \exp[B_{25/50}(1/T_2 - 1/(298,15 \text{ K}))]$		3375		K
B-value	$B_{25/80}$	$R_2 = R_{25} \exp[B_{25/80}(1/T_2 - 1/(298,15 \text{ K}))]$		3411		K
B-value	$B_{25/100}$	$R_2 = R_{25} \exp[B_{25/100}(1/T_2 - 1/(298,15 \text{ K}))]$		3433		K

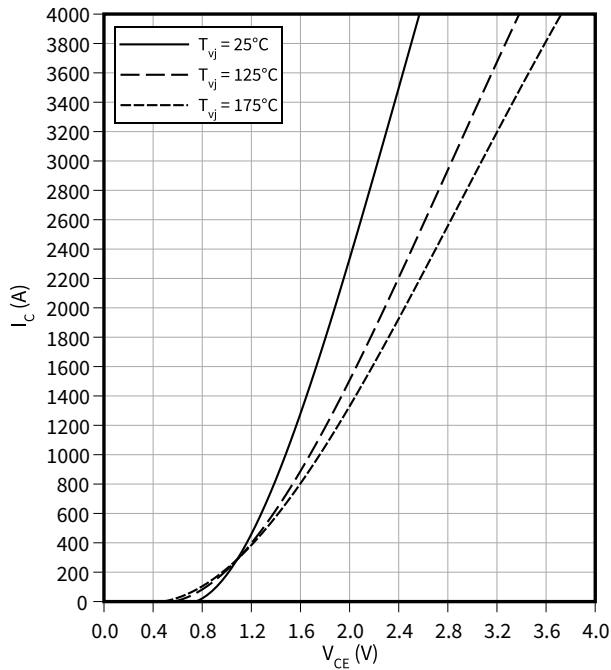
Note: For an analytical description of the NTC characteristics please refer to AN2009-10, chapter 4.

5 Characteristics diagrams

Output characteristic (typical), IGBT, Inverter

$I_C = f(V_{CE})$

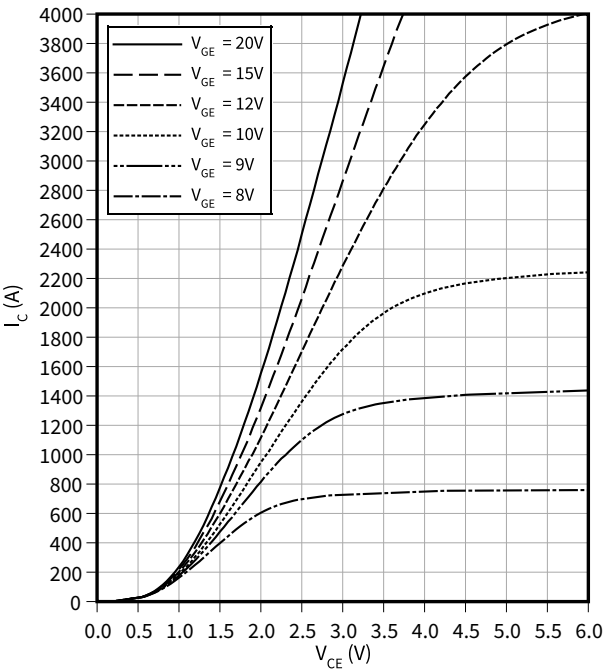
$V_{GE} = 15\text{ V}$



Output characteristic field (typical), IGBT, Inverter

$I_C = f(V_{CE})$

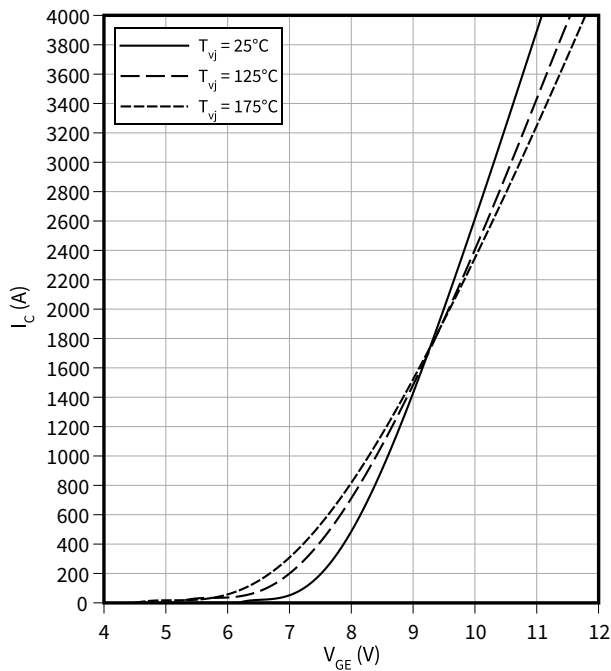
$T_{vj} = 175\text{ °C}$



Transfer characteristic (typical), IGBT, Inverter

$I_C = f(V_{GE})$

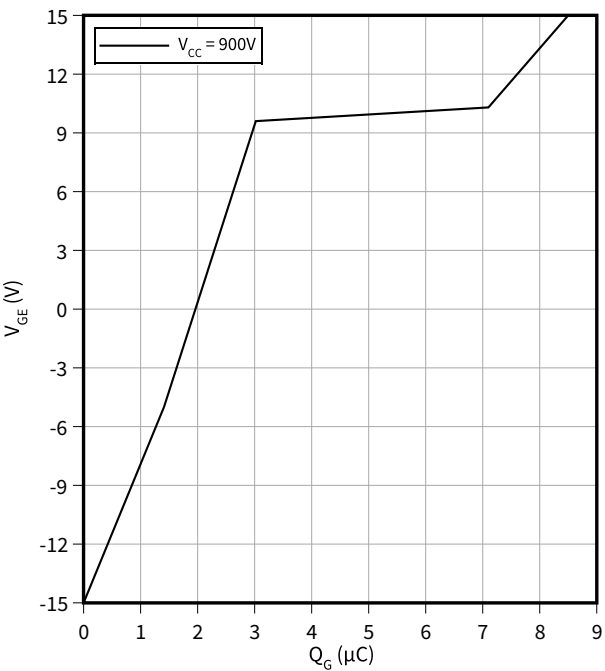
$V_{CE} = 20\text{ V}$



Gate charge characteristic (typical), IGBT, Inverter

$V_{GE} = f(Q_G)$

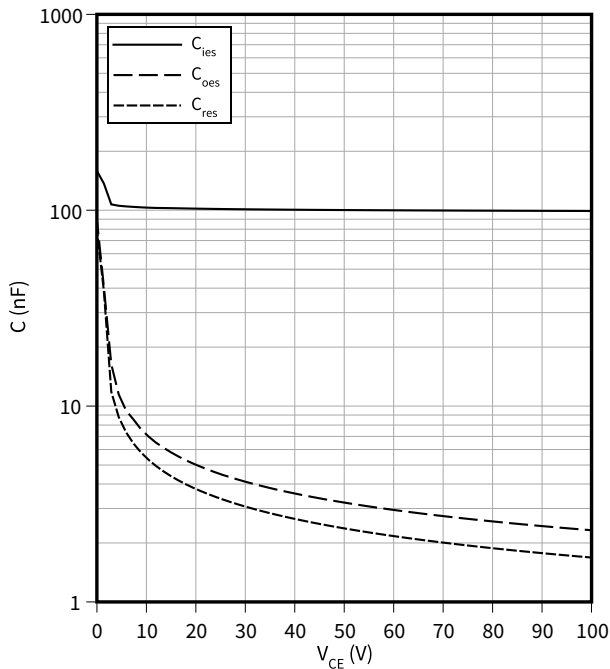
$I_C = 2000\text{ A}, T_{vj} = 25\text{ °C}$



5 Characteristics diagrams

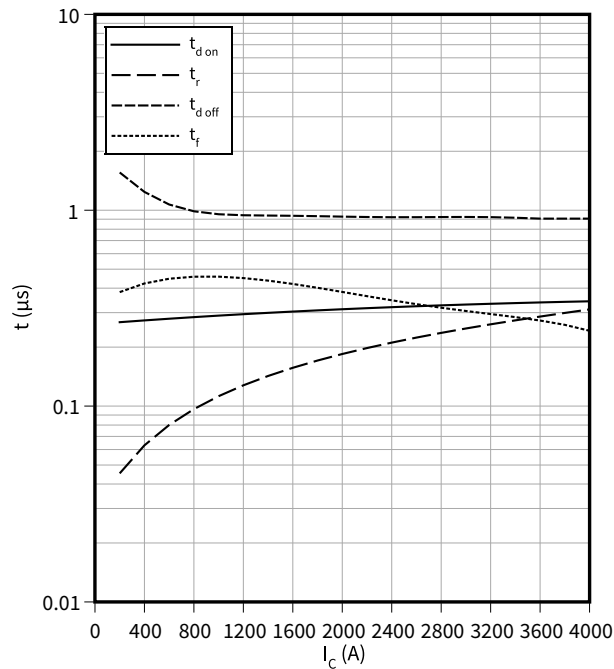
Capacity characteristic (typical), IGBT, Inverter

$C = f(V_{CE})$
 $f = 100 \text{ kHz}$, $V_{GE} = 0 \text{ V}$, $T_{vj} = 25 \text{ }^{\circ}\text{C}$



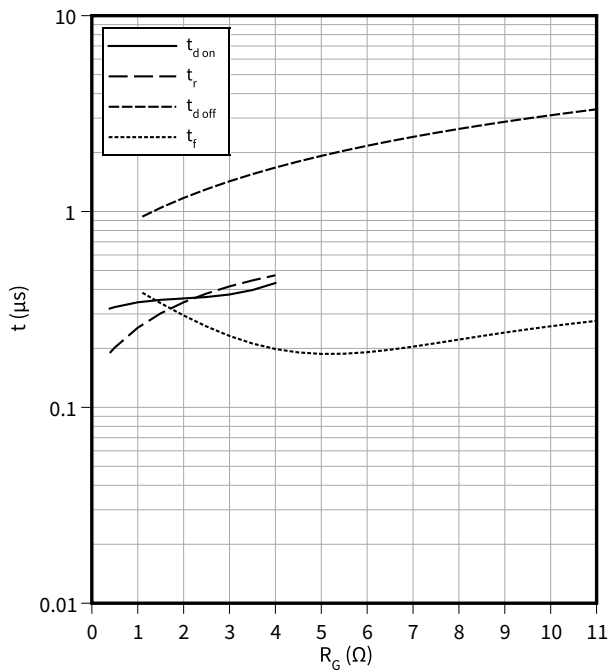
Switching times (typical), IGBT, Inverter

$t = f(I_C)$
 $R_{Goff} = 1.1 \text{ } \Omega$, $R_{Gon} = 0.3 \text{ } \Omega$, $V_{GE} = \pm 15 \text{ V}$, $V_{CC} = 900 \text{ V}$, $T_{vj} = 175 \text{ }^{\circ}\text{C}$



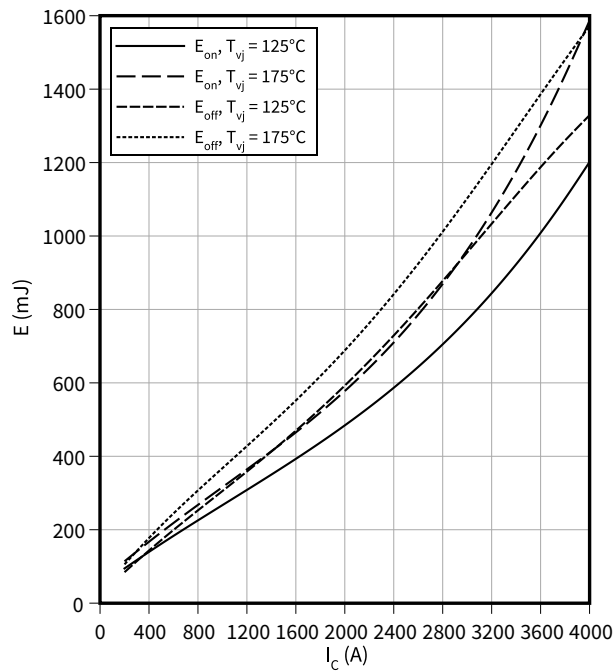
Switching times (typical), IGBT, Inverter

$t = f(R_G)$
 $V_{GE} = \pm 15 \text{ V}$, $I_C = 2000 \text{ A}$, $V_{CC} = 900 \text{ V}$, $T_{vj} = 175 \text{ }^{\circ}\text{C}$



Switching losses (typical), IGBT, Inverter

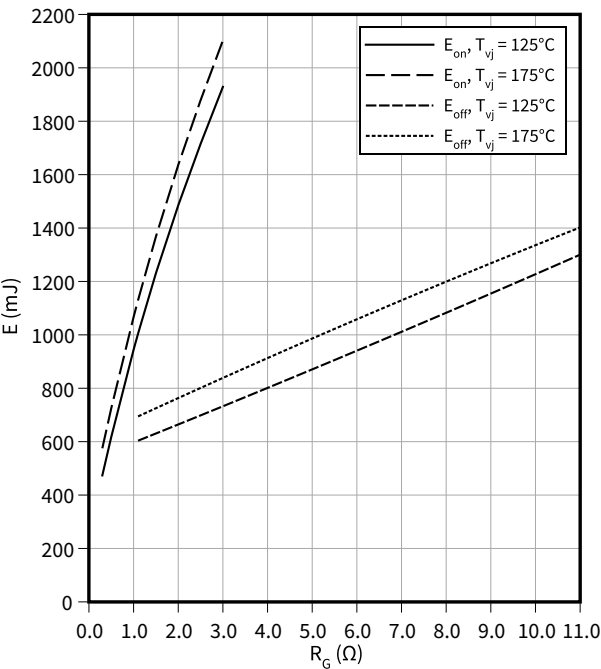
$E = f(I_C)$
 $R_{Goff} = 1.1 \text{ } \Omega$, $R_{Gon} = 0.3 \text{ } \Omega$, $V_{CC} = 900 \text{ V}$, $V_{GE} = \pm 15 \text{ V}$



5 Characteristics diagrams

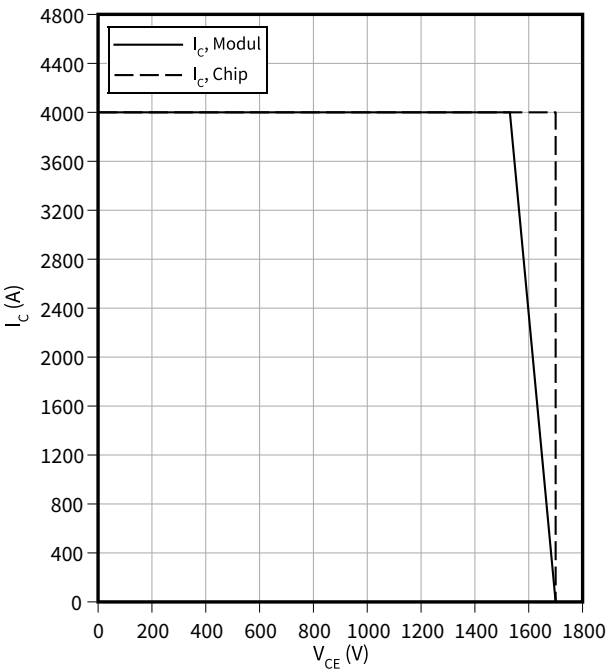
Switching losses (typical), IGBT, Inverter

$E = f(R_G)$
 $I_C = 2000\text{ A}$, $V_{CC} = 900\text{ V}$, $V_{GE} = \pm 15\text{ V}$



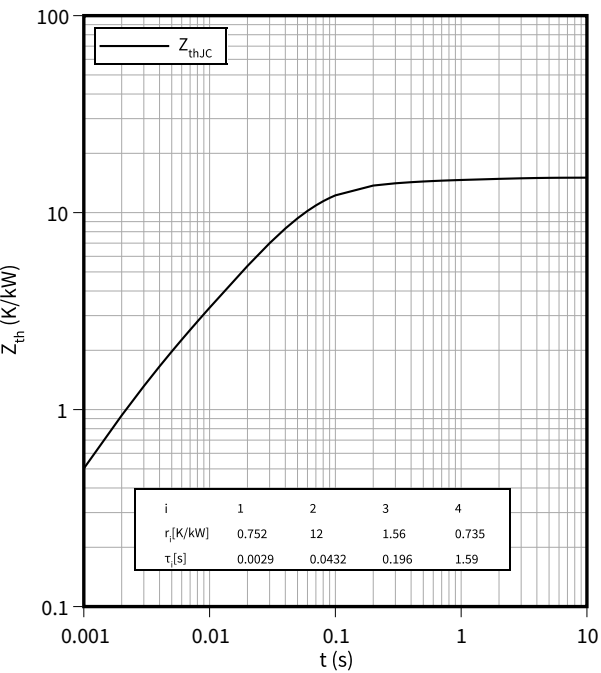
Reverse bias safe operating area (RBSOA), IGBT, Inverter

$I_C = f(V_{CE})$
 $R_{Goff} = 1.1\ \Omega$, $V_{GE} = \pm 15\text{ V}$, $T_{vj} = 175^\circ\text{C}$



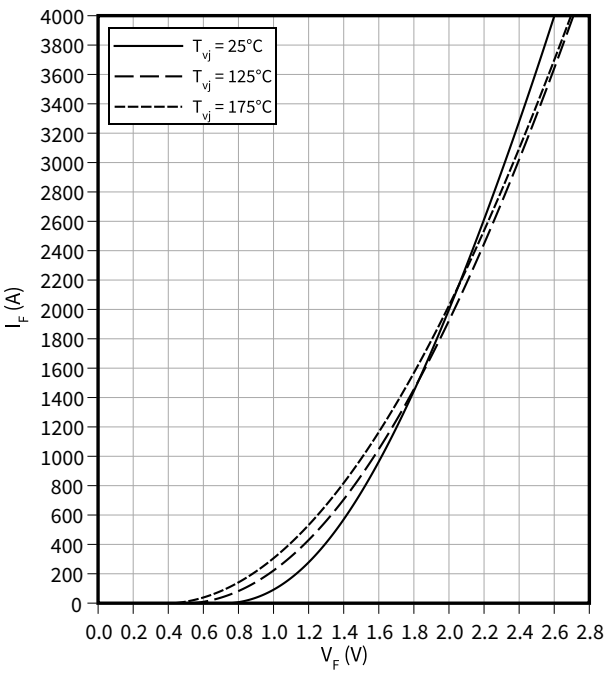
Transient thermal impedance, IGBT, Inverter

$Z_{th} = f(t)$



Forward characteristic (typical), Diode, Inverter

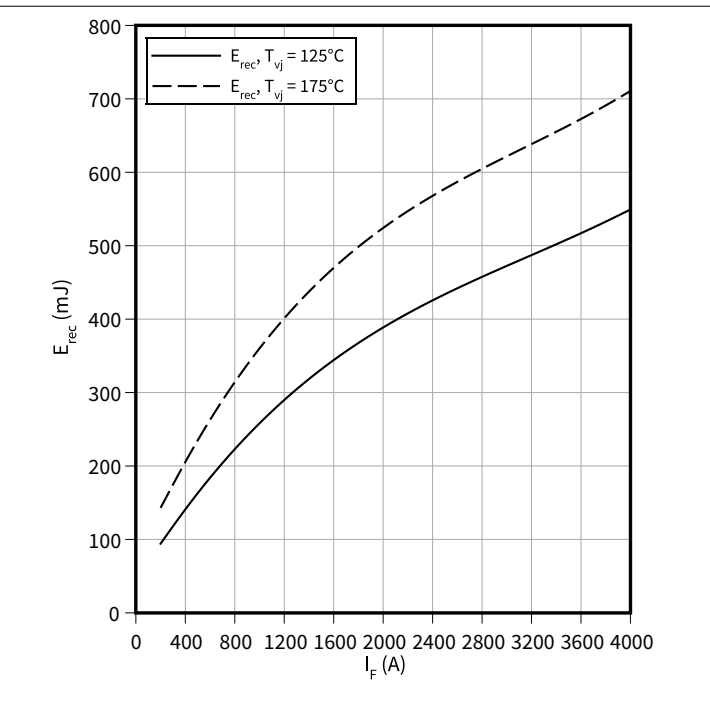
$I_F = f(V_F)$



5 Characteristics diagrams

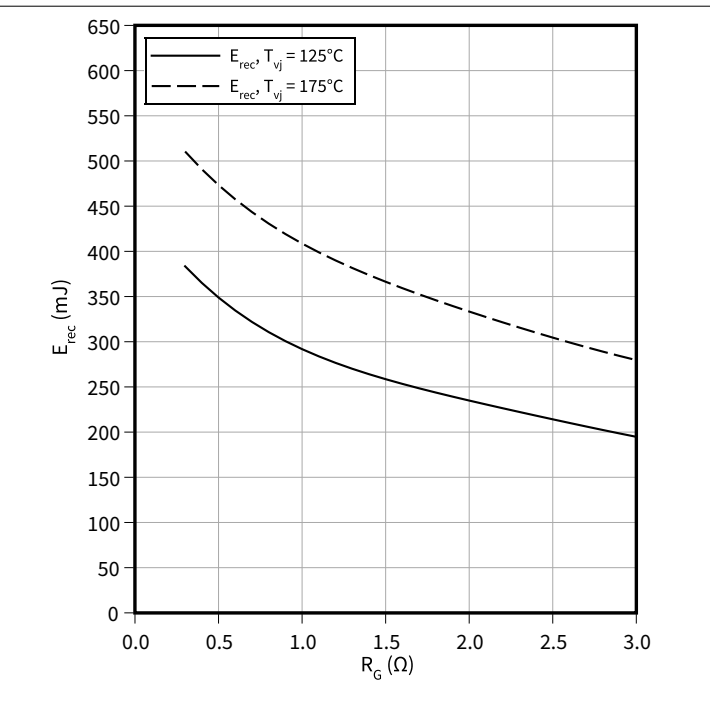
Switching losses (typical), Diode, Inverter

$E_{rec} = f(I_F)$
 $R_{Gon} = R_{Gon}(IGBT)$, $V_{CC} = 900\text{ V}$



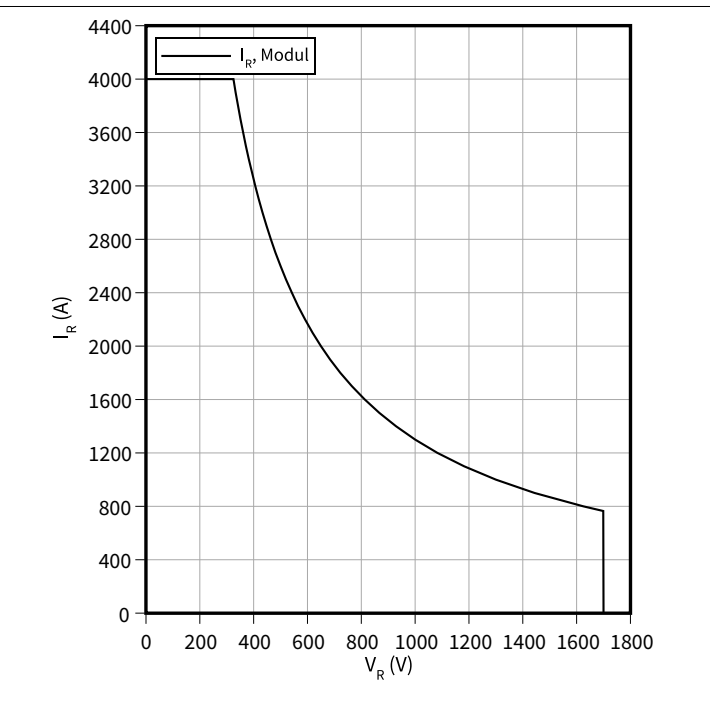
Switching losses (typical), Diode, Inverter

$E_{rec} = f(R_G)$
 $I_F = 2000\text{ A}$, $V_{CC} = 900\text{ V}$



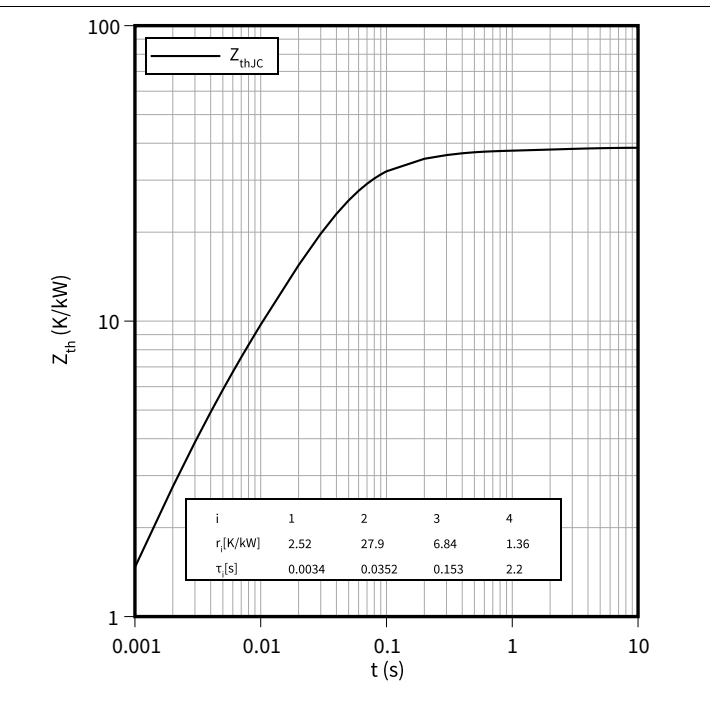
Safe operating area (SOA), Diode, Inverter

$I_R = f(V_R)$
 $T_{vj} = 175\text{ }^\circ\text{C}$



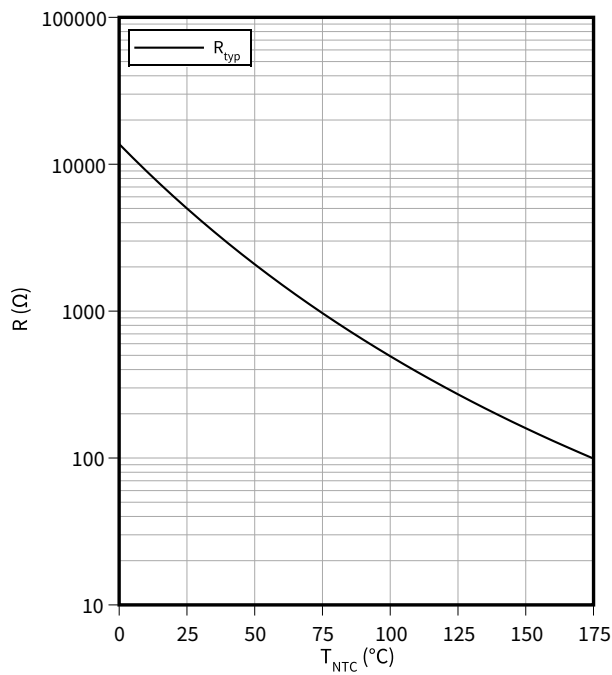
Transient thermal impedance, Diode, Inverter

$Z_{th} = f(t)$



Temperature characteristic (typical), NTC-Thermistor

$R = f(T_{NTC})$



6 Circuit diagram

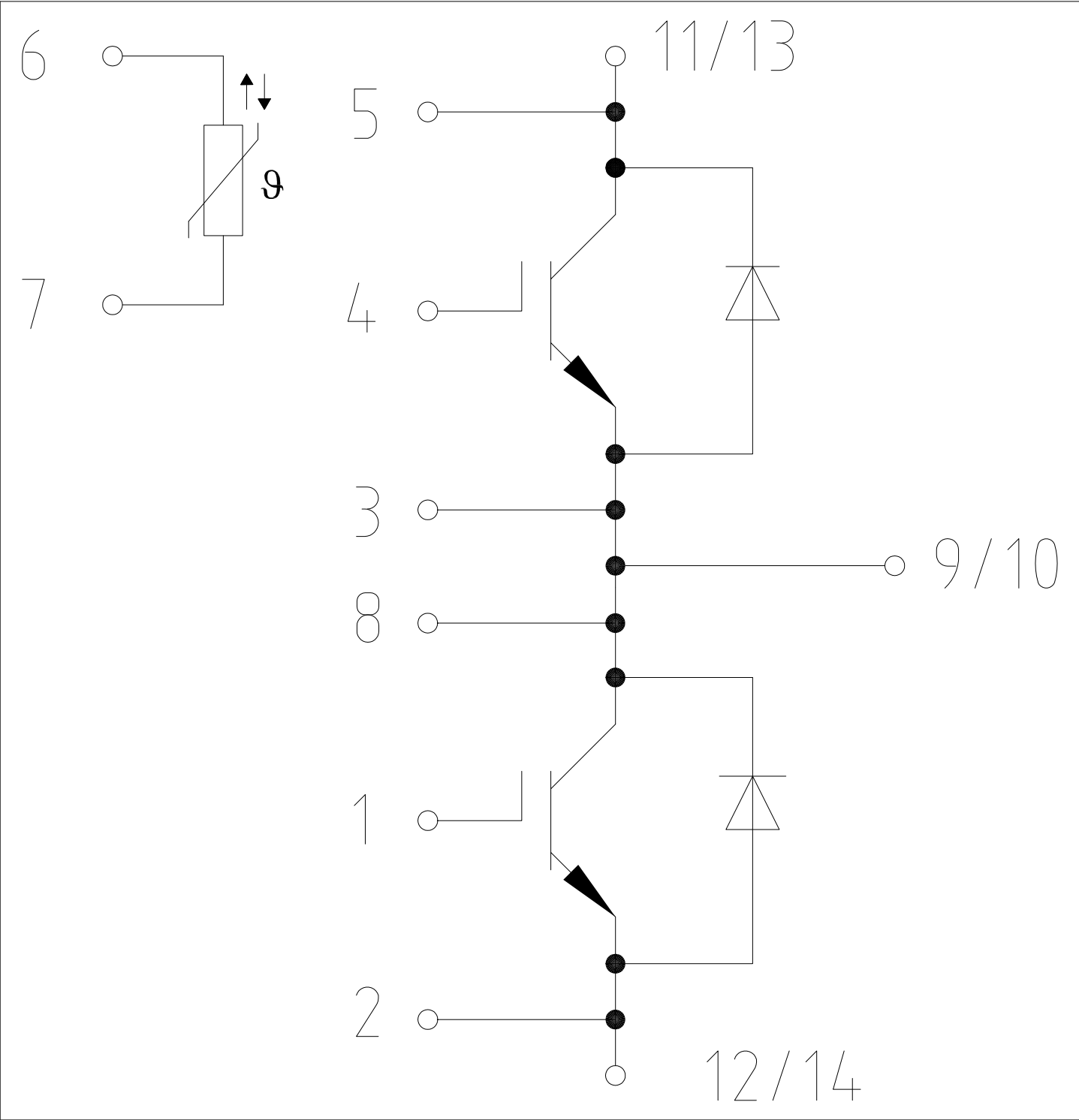


Figure 1

7 Package outlines

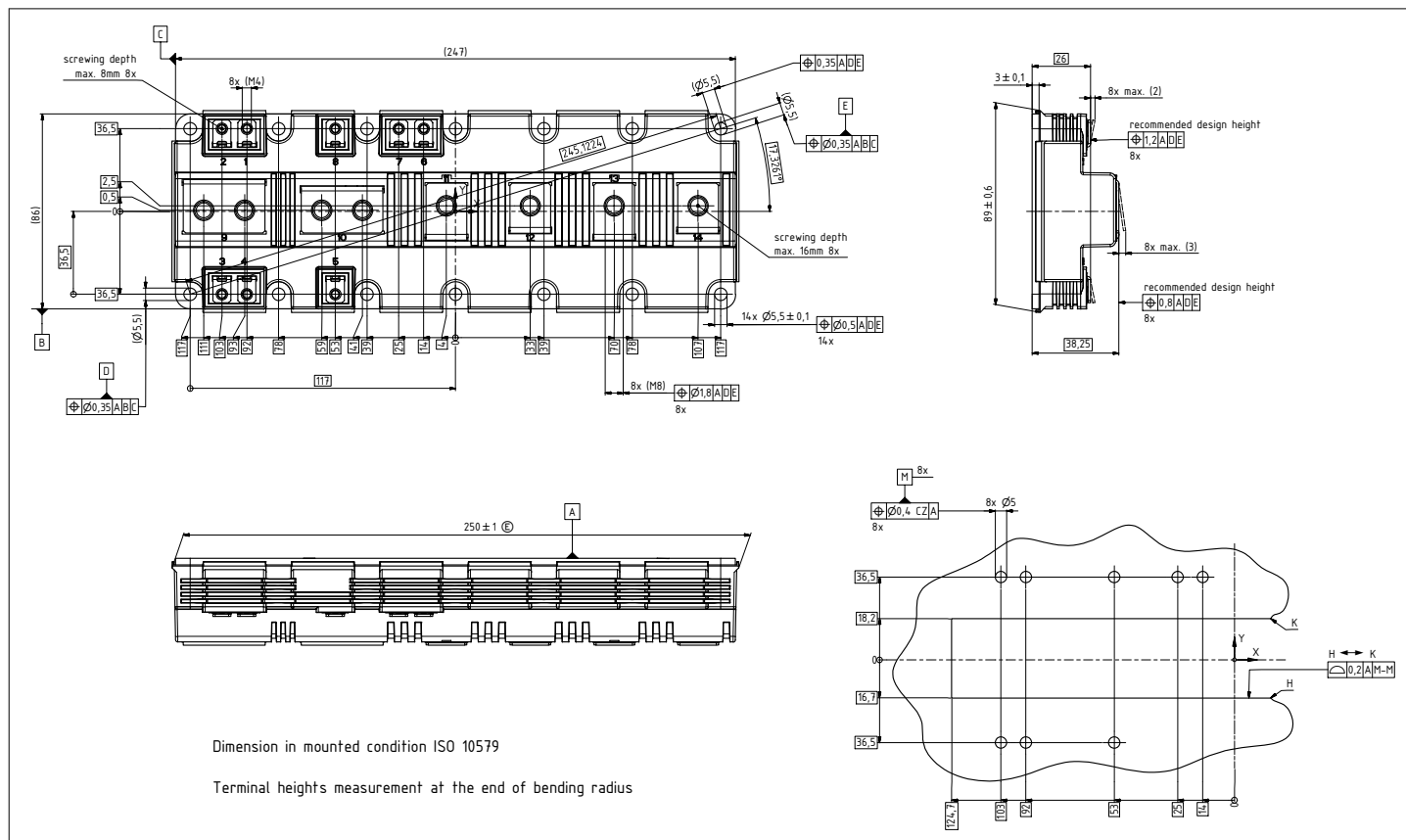


Figure 2

8 Module label code

Module label code			
Code format	Data Matrix		Barcode Code128
Encoding	ASCII text		Code Set A
Symbol size	16x16		23 digits
Standard	IEC24720 and IEC16022		IEC8859-1
Code content	<i>Content</i>	<i>Digit</i>	<i>Example</i>
	Module serial number	1 – 5	71549
	Module material number	6 - 11	142846
	Production order number	12 - 19	55054991
	Date code (production year)	20 – 21	15
	Date code (production week)	22 – 23	30
Example	 71549142846550549911530  71549142846550549911530		

Figure 3

Revision history

Document revision	Date of release	Description of changes
0.10	2022-05-17	Initial version
0.20	2023-01-24	Target datasheet
1.00	2023-05-31	Final datasheet

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